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1	DOI: 10.1002/adfm.201102941
2 3 4	Silaindacenodithiophene based low band gap polymers – the effect of fluorine substitution on device performances and film morphologies.
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24	Keywords: silaindacenodithiophene, hole mobility, solar cell, fluorine, conjugated polymers
25	
26	Abstract: Silaindacenodithiophene is co-polymerized with benzo[c][1,2,5]thiadiazole (BT)
27	and 4,7-di(thiophen-2-yl)benzo[c][1,2,5]thiadiazole (DTBT), respectively their fluorinated
28	$counter\ parts\ 5,6-difluor obenzo \ [c] \ [1,2,5] \ thiadiazole\ (\textbf{2FBT})\ and\ 5,6-difluor o-4,7-di \ (thiophen-2,1), thiadiazole\ (\textbf{2FBT})\ and\ (\textbf{2FBT})\ and$
29	2-yl) benzo[c][1,2,5]thiadiazole (2FDTBT). The influence of the thienyl spacers and fluorine
30	atoms on molecular packing and active layer morphology is investigated with regard to device
31	performances. BHJ solar cells based on silaindacenodithiophene donor-acceptor polymers
32	achieved PCE's of 4.5% and hole mobilities of as high as 0.28 cm ² /(Vs) were achieved in
33	OFET.
34	
35	1. Introduction
36	Over the last decade organic semi-conducting polymers have received a lot of attention, with

their performances in organic field effect transistors (OFET) and organic photovoltaic devices



(OPV) increasing significantly.^[1] The improved performance is not only the result of a better 1 2 understanding of the physics governing the various charge generating and transport processes 3 and the improved processing techniques, but also due to the development of new donor-4 acceptor semiconducting materials.^[2] 5 Silole based building blocks, such as dithienosilole and indacenodithiophene (IDT), have 6 proven their potential in OPVs, as well as in OFETs, when introduced into donor-acceptor polymers. [3] Extended π -conjugated ladder type monomers like indacenodithiophene are 7 8 attractive for incorporation into donor-acceptor polymers partly because the backbone 9 rigidification leads to an improved conjugation length (enhanced coplanarity of repeat units), 10 resulting in higher short-circuit currents (J_{SC}) due to an improved long wavelength photon 11 absorption. Besides the improved optical properties, the silicon bridge stiffens the polymer 12 backbone and reduces conformational disorder. This reduction in energetic disorder has been 13 reported to increase the charge carrier mobility.^[4] Recently the introduction of silicon atoms 14 into the indacenodithiophene backbone was observed to provide high photocurrent efficiencies and high charge carrier mobilities.^[5] In addition, the separation between the anti-15 16 bonding lobes located on the carbon atoms of linked aryl rings in the indacenodithiophene 17 unit increases, and this reduction in antibonding energy manifests as a reduction in the 18 HOMO energy level, thus leading to an increase in the open-circuit voltage $(V_{\rm OC})$ of solar 19 cells. It is also possible in some cases to have effective orbital mixing between the silicon's σ^* -orbital and the π^* -orbital of the adjacent butadiene fragment, stabilizing the LUMO, with 20 21 correspondingly lower bandgaps than their carbon bridged counterparts. [6] 22 Recently, several groups have reported fluorine substituted conjugated polymers with highefficiency solar cells.^[7] Fluorine is smaller in size than other electron withdrawing groups 23 24 (e.g. cyano or trifluoromethyl groups) and can be introduced within the polymer backbone 25 without causing too much steric hindrance.



The co-polymerization of silaindacenodithiophene (SiIDT) with benzo[c][1,2,5]thiadiazole

2 (BT), 4,7-di(thiophen-2-yl)benzo[c][1,2,5]thiadiazole (DTBT) respectively, has led to high

3 $V_{\rm OC}$ values in OPV devices.^[5] We expect to further increase the OPV performances of **SiIDT**

based polymers by increasing the $V_{\rm OC}$ of the aforementioned polymers due to the introduction

of electron-withdrawing fluorine atoms on the polymer backbone, thus lowering the

polymer's HOMO energy level and potentially increasing the PCE.^[7a, 8] Herein we report the

co-polymerization of 5,6-difluorobenzo[c][1,2,5]thiadiazole (**2FBT**) and 5,6-difluoro-4,7-

8 di(thiophen-2-yl) benzo[c][1,2,5]thiadiazole (**2FDTBT**) with the **SiIDT** donor moiety. The

influence of the thienyl spacers and the fluorine atoms on molecular packing and active layer

morphology will be evaluated with regard to device performance.

2. Results and Discussion

2.1. Synthesis

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The silaindacenodithiophene (**SiIDT**) monomer was obtained according to our previously published synthetic pathway. [5b] All four copolymers shown in **Scheme 1** were synthesized by Stille cross-coupling reactions under microwave heating conditions, yet two different catalytic systems and solvents respectively, were used depending on the aryl groups to couple. In the case where the stannylated **SiIDT** monomer was coupled to a phenyl ring, tetrakis(triphenylphosphine) palladium was used as catalyst and *o*-xylene as solvent. However, when the **SiIDT** unit was coupled to a thienyl group, tris(dibenzylideneacetone) dipalladium, together with tri(*o*-tolyl) phosphine was used as catalytic system in chlorobenzene.

It is essential for the performance of OFETs and OPVs to employ high quality semi-

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conducting materials, i.e. the polymer should have no structural defects and contain neither

organic, nor inorganic impurities. By using metal catalyzed coupling reactions, the probability

of structural defects in the polymer chain can be minimized, but there is typically no



deliberate control over the chemical nature of the chain ends, unless an endcapping step at the 1 2 end of the polymerization is used. Even though the concentration of end-groups is very low in a polymer chain of typical molecular weight, their effects on charge trapping, hysteresis and 3 film morphology can be significant.^[9] In order to avoid these undesirable effects, all the 4 5 synthesized polymers were end-capped with chemically inert phenyl groups. Organic and inorganic impurities were removed by precipitating the polymer in methanol, followed by 6 7 Soxhlet extractions with polar and non-polar solvents. After the Soxhlet extractions, the 8 polymer was dissolved in chloroform and washed with an aqueous sodium 9 diethyldithiocarbamate solution to remove residual palladium impurities. 10 All polymers were synthesized with high molecular weights and comparable polymerization 11 degrees, with the **SiIDT-BT** polymer having the highest molecular weight (M_n=30.0 kg/mol). 12 The molecular weights of all polymers are summarized in **Table 1**. The polymers are readily 13 soluble in common organic solvents, except for the fluorinated polymers, which will only 14 dissolve when heated in chlorinated solvents. Thermal gravimetric analysis (TGA) confirmed 15 the stability of all the polymers and a 5% weight loss could not be observed at temperatures 16 lower than 400°C (see Figure S18 in the Supporting Information). Differential scanning 17 calorimetry (DSC) shows a broad melt around 310°C with a sharper crystallisation on cooling 18 at around 290°C for **SiIDT-BT**, but for all the other polymers no obvious thermal transitions 19 were identified in the temperature range of 0 to 350°C (see Figure S19 to S23 in the 20 Supporting Information).

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2.2. Optical Properties

- 23 The UV-vis. absorption spectra of the polymers in dilute chlorobenzene solution and thin-
- 24 films spin-coated on glass substrates are shown in Figure 1. The detailed absorption data,

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1 including absorption maxima in solution and film, as well as the corresponding absorption

2 onsets and bandgaps are presented in **Table 2**.

3 Even though the polymer backbones of **SiIDT-BT** and **SiIDT-2FBT** are very similar and the 4 fluorine atoms are small in size, they have a large influence on the molecular packing. In 5 solution, the absorption feature of **SiIDT-2FBT** is blue-shifted by 40 nm compared to **SiIDT-**6 **BT**. The blue-shift is partially attributed to its lower molecular weight and the presence of fluorine on the benzothiadiazole (BT) unit. The atomic radius of fluorine (0.50 Å) is larger 7 8 than that of hydrogen (0.25 Å) and expected to give rise to steric hindrance between the fluorine atoms on the **BT** unit and the adjacent thiophene of the **SiIDT** moiety. [10] We 9 10 attribute the blue shift of the absorption spectrum to the reduced conjugation length of SiIDT-11 **2FBT**. In the solid state however, the backbone twist is suppressed due to planarising 12 intramolecular interactions between the fluorine atoms on the BT core and the sulfur atom on 13 the neighboring SiIDT unit, resulting in similar absorption peaks for SiIDT-BT and SiIDT-14 **2FBT** with a more pronounced vibronic structure compared to the solution absorption spectra.[11] In the case of SiIDT-DTBT and SiIDT-2FDTBT the influence of the fluorine 15 16 atoms on the backbone twist is diminished because the additional thiophene ring between the 17 SiIDT moiety and the BT core acts as a spacer, thus minimizing the sterical hindrance 18 between the two bulkier aromatic units. 19 Both polymers, SiIDT-BT and SiIDT-2FBT, exhibit two well defined absorption peaks, one at higher energies resulting from π - π * transitions and a more important one at lower energies 20 21 caused by the internal charge transfer (ICT) from the donor to the acceptor part of the polymer backbone. A different behavior can be observed, when thienyl spacers are introduced 22 23 between the donor and acceptor parts of the polymer backbone, as it is the case for SiIDT-24 **DTBT** and **SiIDT-2FDTBT**. The UV-vis. spectra still present two different absorption 25 features, but they are less defined as in the previous case. For both polymers, the π - π *



1 transition peaks are more intense and observed at longer wavelengths, compared to the 2 absorption peaks of SiIDT-BT and SiIDT-2FBT, resembling rather low-wavelength 3 shoulders than independent peaks. 4 The ionization potentials of all polymers were measured by ultraviolet photoelectron 5 spectroscopy in air (UV-PESA) and cyclic voltammetry (CV); the results are summarized in 6 **Table 2.** The measured energy levels follow the same trends within both techniques, but there 7 are significant differences when comparing the data from both techniques. These differences 8 emphasize that it is very difficult to measure the frontier-orbital energy levels accurately 9 because the values obtained depend not only on the experimental technique, but can also be 10 influenced by the morphology, hence, and the measured energy levels should be regarded as estimated values. PESA, as well as CV measurements, confirm that the introduction of 11 12 electron withdrawing fluorine atoms lower both HOMO and LUMO energy levels to a similar 13 degree, and thus have a negligible effect on the bandgap of SiIDT-2FBT and SiIDT-14 **2FDTBT** compared to their non-fluorinated counter-parts. 15 Quantum mechanical calculations were performed to predict the energy levels and model the 16 molecular orbital distributions. Density functional theory calculation, using B3LYP/6-31G* 17 model, were performed on trimers with methyl substituted alkyl chains for simplicity. In our 18 study, the theoretical values were all higher in energy than the experimental values, which we 19 attribute to limitations within the DFT model to describe low-band gap semi-conducting 20 polymers.^[12] Nevertheless, the calculated values are consistent with the trends observed in the 21 experimental PESA and CV data. The calculations predict lower lying HOMO energy levels 22 for the fluorinated polymers, as well as increase in the HOMO when thienyl spacers are 23 introduced between the donor and acceptor parts of the polymer backbone. The theoretical 24 calculations predict furthermore a delocalization of the HOMO over the entire polymer 25 backbone and a preferential localization of the LUMO on the BT moiety for all four BT



- 1 containing polymers. The molecular orbitals of SiIDT-2FBT and SiIDT-2FDTBT are
- depicted in **Figure 2**; the energy distributions for **SiIDT-BT** and **SiIDT-DTBT** can be found

3 in the supporting information.

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2.3. Field-Effect Transistor Devices

Field effect transistors with top-gate, bottom-contact device architecture were fabricated to investigate the charge carrier mobility of SiIDT based polymers. After thermal annealing at 180°C, the hole mobilities were extracted from the transfer characteristics in saturation and are summarized in **Table 3**. The fluorine-sulfur interactions were expected to favor polymer backbone planarization, potentially therefore reducing intermolecular packing distances and thus having a positive effect on hole mobility. However the opposite effect is observed experimentally, both fluorinated polymers (SiIDT-2FBT and SiIDT-2FDTBT) exhibit lower hole mobilities, 0.004 cm²/Vs and 0.19 cm²/Vs, than their non-fluorinated counterparts. It is speculated that the lower electron density on the polymer backbone, induced by the presence of fluorine atoms, hinders hole mobility, or hole injection, which compensates the beneficial effect of backbone planarity. The introduction of thienyl spacers into the polymer backbone however, has a positive effect on the hole mobility (0.28 cm²/Vs and 0.19 cm²/Vs). SiIDT-**DTBT** and **SiIDT-2FDTBT** exhibit several orders of magnitude higher hole mobilities, than the polymers with no spacers in the backbone. The transfer curves and output characteristics of the OFET devices can be found in the Supporting Information. To understand this significant difference in mobility, drop cast polymer films were annealed for 10 minutes at 180°C and probed by X-ray diffraction (XRD). The complete XRD spectra of all four **SiIDT** polymers before and after annealing can be found in the Supporting Information. As can be seen in the diffraction patterns presented in Figure 3, SiIDT-BT and SiIDT-2FBT both show intense diffraction peaks at 5.3° and 10.6°, thus giving evidence for a crystalline



microstructure with a lamellar packing distance of 16.6 Å. Interestingly, the **SiIDT-BT** has a 2 very amorphous microstructure before annealing, and only becomes highly ordered upon 3 annealing at 180°C for 10 minutes. 4 We further investigated OFET devices based on **SiIDT-BT** before and after annealing, but the hole mobility remained virtually unchanged (0.012 cm²/Vs before and 0.014 cm²/Vs after 5 6 annealing). However a considerable shift in threshold voltage from -7 V before to -27 V after 7 annealing was observed. The polymer film morphology was investigated by AFM before and 8 after annealing (See Figure S26 in the Supporting Information) and a surface roughening was 9 noticed. We attribute the threshold voltage increase in part to the possible introduction of new 10 trap states at the dielectric interface formed during the crystallization of the polymer at high 11 annealing temperatures, and corresponding surface roughening. 12 On the other hand, SiIDT-DTBT and SiIDT-2FDTBT were found to be less crystalline than 13 the aforementioned polymers, showing broader and less intense diffraction peaks at 5.1°, 14 respectively 5.3°. The diffraction peak of **SiIDT-DTBT** is sharper (FWHM = 0.46) than the 15 one for **SiIDT-2FDTBT** (FWHM = 1.23), thus indicating a higher degree of crystallinity. In 16 addition, a change in the position of the diffraction peak of SiIDT-DTBT (5.1°) compared to 17 **SiIDT-2FDTBT** (5.3°) is observed, which translates into a larger lamellar stacking distance 18 of 17.4 Å. It is worth mentioning, that in this study the least crystalline polymers, SiIDT-19 **DTBT** and **SiIDT-2FDTBT**, gave the highest mobilities. In previously published reports it has also been found that polymers that do not exhibit a high degree of long range order can 20 21 lead to high hole mobilities, believed to be due to excellent one dimensional transport along 22 the polymer backbone with short favourable hops between chains facilitating charge percolation.[13] 23 24

3.4. Photovoltaic Properties

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To evaluate the photovoltaic performances of the SiIDT polymers, bulk hetero-junction 1 2 (BHJ) cells with conventional solar device structure consisting of ITO/PEDOT:PSS/Polymer:PC71BM/Ca/Al were prepared and tested under simulated 100 mW 3 4 cm⁻² AM1.5G illumination. The J-V curves and external quantum efficiencies (EQE) of the 5 organic photovoltaic cells (OPV) are presented in Figure 4. The corresponding open-circuit 6 voltages $(V_{\rm OC})$, short-circuit currents $(J_{\rm SC})$, fill factors (FF) and power conversion efficiencies 7 (PCE) are summarized in **Table 4**. 8 Figure 4 shows the external quantum efficiency (EQE) of the best devices of each blend ratio 9 as a function of wavelength, which is consistent with the polymer/fullerene blends UV-vis. 10 absorption spectra. Convolution of these EQE spectra with the AM1.5 spectra gave calculated short circuit current densities in good agreement (±0.5 mA cm⁻²) with those measured under 11 12 AM1.5 simulated sunlight (Table 4). The EQE spectrum of SiIDT-DTBT and SiIDT-13 **2FDTBT** extends further to the red than **SiIDT-BT**, consistent with the insertion of thienyl 14 spacer leading to extended red absorption in these polymers. The EQE of both of these 15 polymers extends up to 700 nm, while that of **SiIDT-BT** ranges only to 650 nm. We attribute 16 the higher EQE response in the visible region to the corresponding strong absorbance of the 17 blends, resulting from both the intrinsic absorption of the polymers and the presence of a high 18 content of PC₇₁BM, which absorbs significantly at 400-500 nm. The broad coverage of the 19 solar spectrum of the solar cell results in a desirable J_{SC} under illumination with white light. 20 The device of **SiIDT-BT** blend exhibited a higher EQE response relative to other polymer 21 blends with a maximum of 60% at about 518 nm, consistent to its higher photocurrent. 22 Devices based on SiIDT-BT and SiIDT-DTBT have been reported previously, with device efficiencies of up to 4.5%.^[5] We expect to further increase the device performance by 23 24 introducing fluorine atoms on the polymer backbone. However, the PCE of the device based 25 on **SiIDT-2FBT** is heavily limited by its low J_{SC} , despite the fact that the UV-vis. absorption



1 spectrum of SiIDT-2FBT is slightly more red-shifted than the SiIDT-BT one. The EQE 2 spectra indicate that this loss of photocurrent results from a loss of photocurrent density from 3 both polymer and PC71BM absorption. Photoluminescence (PL) quenching data indicated 4 similar high polymer PL quenching for both polymers, indicating that this loss of 5 photocurrent cannot be assigned to exciton diffusion limitations (see **Figure 5**). To evaluate 6 further the lower J_{SC} for the SiIDT-2FBT /PC₇₁BM device, the blend morphologies were 7 investigated by close contact atomic force microscopy (AFM), as shown in **Figure 6**. While 8 the topography image of SiIDT-BT/PC71BM shows a relative homogeneous film 9 microstructure, large phase segregation (50-200 nm) is found in the topography image of 10 SiIDT-2FBT/PC₇₁BM. Transmission electron microscopy (TEM) confirmed this difference in 11 film microstructure, with excellent agreement between the AFM and TEM data (see **Figure 6**). 12 The TEM data employed an iodine stain, with the more prevelant darker island evident in the 13 TEM image corresponding to PC₇₁BM rich domains. A similar phenomenon was observed by 14 Yu and co-workers, who found that introducing fluorine to the polymer backbone changes 15 initially homogenous blend morphology to a heterogeneous one with large phase segregation and non-bicontinuous features.^[14] The extent to which the coarse film microstructure is the 16 17 direct cause of the lower photocurrent for SiIDT-2FBT/PC71BM is not obvious. The PL 18 quenching data indicates that the lower photocurrent is most probably not associated with 19 exciton diffusion limitations, suggesting that the domains observed in the AFM and TEM 20 images do not correspond to pure polymer and pure fullerene domains. Rather it appears more 21 likely that this coarser domain structure reduces the efficiency of charge collection in the 22 **SiIDT-2FBT**/PC₇₁BM devices. 23 Although the HOMO energy levels for SiIDT-BT and SiIDT-2FBT measured by PESA and 24 CV are very similar, a slightly larger $V_{\rm OC}$ is observed in the devices based on **SiIDT-2FBT** as 25 expected from the DFT calculations. Devices based on **SiIDT-DTBT** display lower $V_{\rm OC}$ than



- SiIDT-BT based devices due to the addition of the thienyl spacer, which primarily increases
- 2 the π electron density, thus raising the HOMO energy level. The introduction of thienyl
- 3 spacers into the polymer backbone also results in a finer blend microstructure (see **Figure 6**).
- 4 SiIDT-DTBT based devices have similar J_{SC} and FF values as the SiIDT-BT polymer but the
- 5 overall device performance is lower because of the smaller $V_{\rm OC}$.
- 6 When devices employ SiIDT-2FDTBT, the addition of the thienyl spacers leads again to a
- 7 smaller V_{OC} compared with **SiIDT-2FBT** based devices. However, there are significant
- 8 improvements in both J_{SC} and FF which increase the device efficiency to 4.3%. The increase
- 9 in photocurrent may be attributed to the red-shifted polymer absorption spectrum.
- Additionally, thienyl spacer introduction offers a much more homogeneous microstructure to
- 11 **SiIDT-2FDTBT**/PC₇₁BM compared with **SiIDT-2FBT**/PC₇₁BM (see **Figure 6**).

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4. Conclusion

- 14 In conclusion, we have synthesized a series of low-band gap polymers incorporating the
- 15 **SiIDT** donor moiety and we investigated the effect of polymer fluorination on device
- 16 performance and morphology. The incorporation of fluorine atoms to the polymer backbone
- was shown to influence both the polymer electronic energy levels and thin film morphology.
- 18 The highest OPV device PCE achieved was 4.3% for the SiIDT-2FDTBT polymer,
- 19 compared to 3.6% for its non-fluorinated counterpart. In field effect transistor devices, the
- 20 **SiIDT** based polymers achieved high hole mobilities, up to 0.28 cm²/Vs, with the unexpected
- 21 trend being that the less crystalline thin films exhibited the higher mobilities.

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5. Experimental Section

- 24 Characterization: Photo Electron Spectroscopy in Air (PESA) measurements were recorded
- 25 with a Riken Keiki AC-2 PESA spectrometer with a power setting of 5nW and a power



1 number of 0.5. Number-average (M_n) and weight-average (M_w) molecular weights were determined with an Agilent Technologies 1200 series GPC in chlorobenzene at 80 °C, using 2 3 two PL mixed B columns in series, and calibrated against narrow polydispersity polystyrene 4 standards. Electron Ionization mass spectrometry were performed with a Micromass 5 AutoSpec Premier mass spectrometer. UV-Vis absorption spectra were recorded on a UV-6 1601 Shimadzu UV-Vis spectrometer. AFM was performed on a 5500 AFM from Agilent 7 Technology in tapping mode and TEM images were recorded on a high-resolution JEOL 2010 8 TEM (80-200 kV) with interchangeable pole-pieces. DSC experiments were carried out with a 9 Metler Toledo DSC822 instrument. TGA plots were obtained with a Perkin Elmer Pyris 1 10 TGA. Cyclic voltammograms (CV) were obtained using a cylindrical platinum working 11 electrode and a platinum mesh counter electrode in acetonitrile at a potential scan rate of 10 12 mV·s⁻¹. Ag/Ag⁺ was used as reference electrode and calibrated against ferrocene. All the 13 measurements were carried out in an argon-saturated solution of 0.1 M of 14 tetrabutylammonium hexafluorophosphate (n-Bu₄NPF₆) in anhydrous acetonitrile. X-ray 15 diffraction (XRD) measurements were carried out with a PANALYTICAL X'PERT-PRO 16 MRD diffractometer equipped with a nickel-filtered Cu Kα₁ beam and a X' CELERATOR 17 detector, using a current of 40 mA and an accelerating voltage of 40 kV. 18 Polymer Synthesis: Condition A. A microwave vial was charged with bis(trimethylstannyl) 19 monomer 1 (0.250 g, 0.233 mmol), 0.95 eq. of dibrominated monomer and 5 mol% of 20 tetrakis(triphenylphosphine) palladium (0). The vial was sealed and 1 mL of o-xylene was 21 added. The reaction mixture was degassed with argon during 30 minutes and submitted to the 22 following temperature scheme in the microwave reactor: 5 minutes at 120°C, 5 minutes at 23 140°C, 5 minutes at 160°C and 40 minutes at 170°C. The reaction mixture was cooled down 24 to room temperature and 0.1 eq. of bromobenzene was added in one portion by syringe. The 25 mixture was resubmitted to the microwave reactor, 1 minute at 100°C, 1 minute at 120°C, 2



minutes at 140°C and 5 minutes at 160°C. Once the polymeric solution was cooled down, 0.1 1 2 eq. of trimethyl(phenyl)stannane was added by syringe. The reaction mixture was subjected 3 on last time to the previously mentioned temperature scheme to finalize the end-capping 4 reaction. After reaction, the crude polymer was precipitated in methanol and then further 5 purified by Soxhlet extractions with acetone, hexane and chloroform, each for 24 hours. 6 Remaining palladium residues were removed by treating a polymeric chloroform solution 7 with an aqueous sodium diethyldithiocarbamate solution for 2 hours at 50°C under vigorous 8 stirring. Afterwards the organic phase was separated from the aqueous phase and washed 9 several times with water. The polymeric solution was concentrated under reduced pressure 10 and precipitated into cold methanol. The recovered polymer was dried under high vacuum for 11 at least 24 hours. 12 Condition B. A 5 mL microwave vial was charged with with bis(trimethylstannyl) monomer 13 1 (0.250 g, 0.233 mmol), 0.95 eq. of dibrominated monomer, 2 mol% 14 tris(dibenzylideneacetone)dipalladium (0) and 8 mol% of tri(o-tolyl) phosphine. The vial was 15 sealed and chlorobenzene (1 mL) was added. The obtained solution was degassed with argon 16 during 30 minutes. The vial was subjected to the following reaction conditions in the microwave reactor: 2 minutes at 100°C, 2 minutes at 120°C, 5 minutes at 140°C, 5 minutes at 17 18 160°C and 40 minutes at 170°C. The polymer was end-capped by addition of 0.1 eq. of 19 bromobenzene before the reaction mixture was resubmitted to the microwave reactor, 1 minute at 100°C, 1 minute at 120°C, 2 minutes at 140°C and 5 minutes at 160°C. The 20 21 polymeric solution was cooled down and 0.1 eq. of trimethyl(phenyl) stannane was added by 22 syringe. The reaction vial was subjected to the previously mentioned temperature scheme to 23 finalize the end-capping reaction. After reaction, the crude polymer was precipitated in 24 methanol and then further purified by Soxhlet extractions with acetone, hexane and 25 chloroform during 24 hours each. Remaining palladium residues were removed by treating a



- polymeric chloroform solution with an aqueous sodium diethyldithiocarbamate solution for 2
- 2 hours at 50°C under vigorous stirring. Afterwards the organic phase was separated from the
- 3 aqueous phase and washed several times with water. The polymeric solution was concentrated
- 4 under reduced pressure and precipitated into cold methanol. The polymer was filtered off and
- 5 dried under high vacuum for at least 24 hours.
- 6 SiIDT-BT. Dark-blue solid (135 mg, 0.131 mmol, 59%). $M_n = 30.0 \text{ kg mol}^{-1}$, $M_w = 58.9 \text{ kg}$
- 7 mol⁻¹, PDI = 1.96. ¹H NMR (o-DCB-d₄, 400 MHz, 313 K, δ): 8.73 (s, 2H), 8.30 (s, 2H), 8.20-
- 8 7.75 (bm, 2H), 1.91-1.71 (bm, 8H, SiCH₂), 1.63-1.50 (bm, 8H, CH₂), 1.49-1.18 (bm, 40H,
- 9 CH₂), 1.04 (t, J = 7 Hz, 12H, CH₃).
- 10 SiIDT-DTBT. Dark-blue solid (151 mg, 0.13 mmol, 63%). $M_n = 22.3 \text{ kg mol}^{-1}$, $M_w = 56.6$
- ld kg mol⁻¹, PDI = 2.54. ¹H NMR (o-DCB-d₄, 400 MHz, 313 K, δ): 8.31 (s, 2H, Ar H), 8.19-8.07
- 12 (m, 2H, Ar H), 8.01-7.83 (bm, 2H, Ar H), 7.80-7.71 (m, 2H, Ar H), 7.67-7.45 (bm, 2H, Ar H),
- 13 1.85-1.69 (bm, 8H, CH₂), 1.61-1.52 (bm, 8H, CH₂), 1.50-1.23 (bm, 40H, CH₂), 1.07 (t, J =
- 14 7 Hz, 12H, CH₃).
- 15 SiIDT-2FBT. Dark-blue solid (102 mg, 0.11 mmol, 51%). $M_n = 21.0 \text{ kg mol}^{-1}$, $M_w = 35.3 \text{ kg}$
- 16 mol⁻¹, PDI = 1.68. ¹H NMR (o-DCB-d₄, 400 MHz, 313 K, δ): 8.91 (s, 2H, Ar H), 8.36 (s, 2H,
- 17 Ar H), 1.94-1.68 (bm, 8H, CH₂), 1.63-1.50 (bm, 8H, CH₂), 1.49-1.25 (bm, 40H, CH₂), 1.05 (t,
- 18 J = 7 Hz, 12H, CH₃).
- 19 SiIDT-2FDTBT. Dark-blue solid (142 mg, 0.12 mmol, 55%). $M_n = 26.4 \text{ kg mol}^{-1}$, $M_w = 71.0$
- 20 kg mol⁻¹, PDI = 2.69. ¹H NMR (o-DCB-d₄, 400 MHz, 313 K, δ): 8.52 (s, 2H, Ar H), 8.24-7.97
- 21 (m, 2H, Ar H), 7.88-7.44 (bm, 4H, Ar H), 1.86-1.71 (bm, 8H, CH₂), 1.69-1.27 (bm, 48H,
- 22 CH₂), 1.17-1,01 (m, 12H, CH₃).
- 23 Device Fabrication and Testing: Top-gate, bottom-contact organic field effect transistors
- 24 (FETs) were fabricated on glass with pentafluorobenzenethiol (PFBT) treated Au electrodes,
- 25 CYTOP (900 nm) dielectric and Al gate. Polymer films were spin cast from o-



dichlorobenzene (10 mg/mL) solutions at a speed of 2000 rpm and annealed at 180 °C for 10 1 2 minutes. The carrier mobility of the films was assessed by measuring transfer curves in 3 saturation ($V_{DS} = -60 \text{ V}$) using a Keithley 4200 semiconductor parameter analyzer. The 4 saturation mobility was determined by fitting a linear relationship of the square root of the 5 drain current to gate potential in the range of -40 to -60 V and averaged over 3 devices. 6 All organic photovoltaic devices have a conventional device architecture, 7 ITO/PEDOT:PSS/Polymer: PC71BM/Ca/Al. The precoated ITO glass substrates were cleaned 8 with acetone and isopropyl alcohol under sonification, followed by drying and oxygen plasma 9 treatment during 7 minutes. A 30 nm layer of PEDOT:PSS was spin-coated onto the plasma-10 treated ITO substrate and baked at 150°C for 20 minutes. An 80 nm active layer consisting of 11 a 1:3 blend of polymer, respectively 1:3.5 for the **SiIDT-BT** polymer, and PC₇₀BM dissolved 12 in o-dichlorobenzene (ODCB) was spin-coated on the PEDOT:PSS layer and then Ca (30 13 nm)/Al (100 nm) cathode was finally deposited by thermal evaporation under high vacuum (10⁻⁶ mbar) through a shadow mask. The pixel size, defined by the spatial overlap of the ITO 14 anode and Ca/Al cathode, was 0.045 cm². The device characteristics were obtained using a 15 16 xenon lamp at AM1.5 solar illumination (Oriel Instruments). Short circuit currents under 17 AM1.5G conditions were obtained from the spectral response and convolution with the solar 18 spectrum, measured with a Keithley source meter. Spectral response was measured under 19 operation conditions using bias light from a 532 nm solid state laser (Edmund Optics). 20 Monochromatic light from a 100 W tungsten halogen lamp in combination with 21 monochromator (Oriel, Cornerstone 130) was modulated with a mechanical chopper. The 22 response was recorded as the voltage over a 50 Ω resistance, using a lock-in amplifier 23 (Stanford research Systems SR830). A calibrated Si cell was used as reference. All the device

Supporting Information

24

25

measurements were carried out behind a quartz window in a nitrogen filled container.



1 Supporting Information is available from the Wiley Online Library or from the author.

2 Acknowledgements

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1 **Figures and captions:** 2

3

4 5

- 6 Scheme 1. Synthesis of the SiIDT based polymers; polymerization condition A: Pd(PPh₃)₄, o-
- 7 xylene, microwave heating; polymerization condition B: Pd₂(dba)₃, P(o-tol)₃, chlorobenzene,
- 8 microwave heating.

9

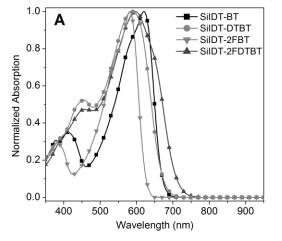
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11 **Table 1.** Molecular weights and thermal properties of the polymers.

Polymer	M _n [kg/mol] [a]	M _w [kg/mol] [a]	PDI [a]	DP_n	T _d [°C] [b]
SiIDT-BT	30.0	58.9	1.96	34	443
SiIDT-DTBT	22.3	56.6	2.54	21	444
SiIDT-2FBT	21.0	35.3	1.68	23	428
SiIDT-2FDTBT	26.4	71.0	2.69	24	431

- 12 [a] Determined by GPC using polystyrene standards and chlorobenzene as eluent. [b] 5%
- weight loss temperatures measured by TGA under nitrogen atmosphere.





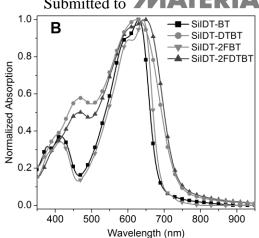


Figure 1. Normalized UV-vis. absorption spectra of **SiIDT** based polymers in dilute chlorobenzene solution (**A**) and thin-film (**B**), spin-cast from chlorobenzene.

Table 2. Optical properties and experimental and calculated energy levels of **SiIDT** based polymers.

			PESA	Cyclic voltammetry	DFT			
Polymer	λ _{max} soln. [nm] [a]	λ _{max} film [nm] [b]	HOMO / LUMO [eV] [c]	HOMO / LUMO [eV]	HOMO / LUMO [eV]	Eg ^{opt} [eV]	E _g EC [eV]	Eg ^{calc} [eV]
SiIDT-BT	412, 620	414, 634	-5.4 / -3.6	-5.3 / -3.1	-4.7 / -3.0	1.8	2.2	1.7
SiIDT-DTBT	454, 588	468, 625	-5.0 / -3.3	-5.2 / -3.4	-4.6 / -3.0	1.7	1.8	1.6
SiIDT-2FBT	381, 582	413, 642	-5.4 / -3.6	-5.3 / -3.1	-4.8 / -3.1	1.8	2.2	1.7
SiIDT-2FDTBT	457, 597	468, 648	-5.1 / -3.4	-5.2 / -3.2	-4.7 / -3.1	1.7	2.0	1.6

- 8 [a] Measured in dilute chlorobenzene solution. [b] Spin-coated from 5 mg/mL chlorobenzene
- 9 solution. [c] The LUMO energy is estimated by adding the absorption onset to the HOMO.

1 1



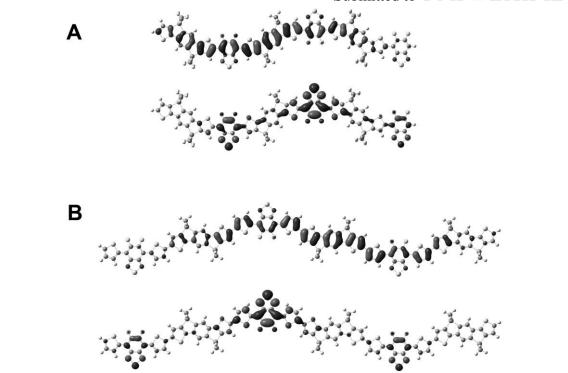


Figure 2. Energy-minimized structure (B3LYP/6-31G*) of a methyl-substituted **SiIDT-2FBT**

(A) & SiIDT-2FDTBT (B) trimer with a visualisation of the HOMO (top) and LUMO

4 (bottom) energy distributions.

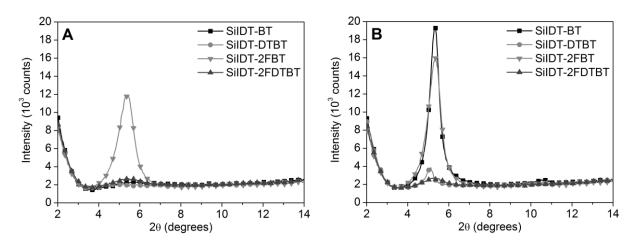


Figure 3. X-ray diffraction (XRD) patterns of drop-cast films of pristine **SiIDT** polymers on glass substrates (A) and after annealing at 180°C for 10 minutes under nitrogen atmosphere (B).



Table 3. OFET Device Characteristics of **SiIDT** polymers.

Polymer	μ_{sat} [cm ² /Vs] [a]	μ_{lin} [cm²/Vs] [b]	I _{on} /I _{off} [a]
SiIDT-BT	0.014	0.011	~104
SiIDT-DTBT	0.28	0.25	~10³
SiIDT-2FBT	0.004	0.002	~10³
SiIDT-2FDTBT	0.19	0.10	~104

- 3 [a] μ_{sat} refer to the highest effective hole mobilities measured in the saturation regime. [b] μ_{lin}
- 4 refer to the highest effective hole mobilities measured in the linear regime. The on-to-off
- 5 ratios (I_{on}/I_{off}) were extracted from the linear regime.

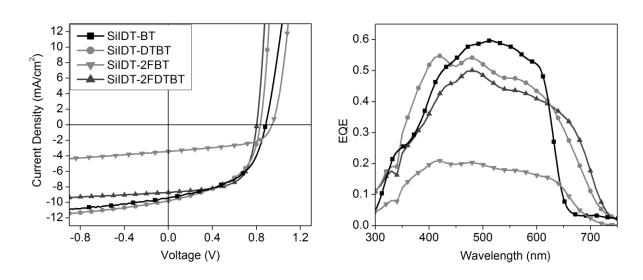
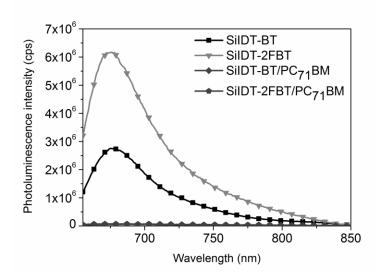


Figure 4. (left) J-V characteristics of SiIDT polymer:PC₇₁BM solar cell under AM1.5 solar

9 illumination and (right) external quantum efficiencies of the cells.





2 Figure 5. Photoluminescence spectra of thin films of SiIDT-BT, SiIDT-2FBT, SiIDT-

BT/PC₇₁BM and SiIDT-2FBT/PC₇₁BM. The samples were excited at 640 nm.

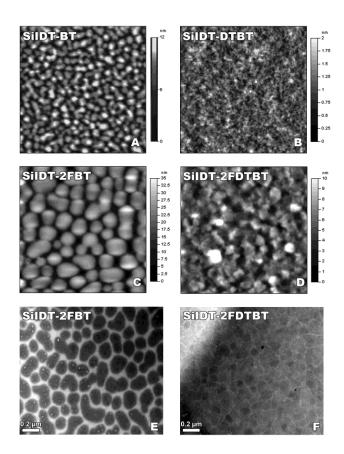


Figure 6. A to D: AFM topography images (2.0 μm x 2.0 μm) of 1:3w/w polymer/PC₇₁BM

7 blends (except for **SiIDT-BT** which is a 1:3.5 polymer:PC₇₁BM blend). E and F: TEM images

8 of **SiIDT-2FBT** and **SiIDT-2FDTBT**.



Table 4. OPV Device Characteristics of **SiIDT** polymers

Polymer	J _{SC} [mA/ cm ²]	V _{oc} [V]	FF	PCE [%]
SiIDT-BT	9.93	0.88	0.52	4.5
SiIDT-DTBT	8.75	0.83	0.50	3.6
SiIDT-2FBT	3.44	0.94	0.54	1.7
SiIDT-2FDTBT	8.36	0.80	0.64	4.3



The table of contents entry.

Fluorine is introduced into silaindacenodithiophene based semi-conducting polymers with the

aim to improve the photovoltaic as well as the charge carrier properties. The influence of the

thienyl spacers and fluorine atoms on molecular packing and active layer morphology of the

Keywords: silaindacenodithiophene, hole mobility, solar cell, fluorine, conjugated polymers

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Silaindacenodithiophene based low band gap polymers – the effect of fluorine substitution on

new polymers is investigated with regard to device performances.

device performances and film morphologies.